

2SJ246 , 2SJ246

SILICON P-CHANNEL MOS FET

Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4V gate drive device can be driven from 5V source.
- Suitable for Switching regulator, DC – DC converter

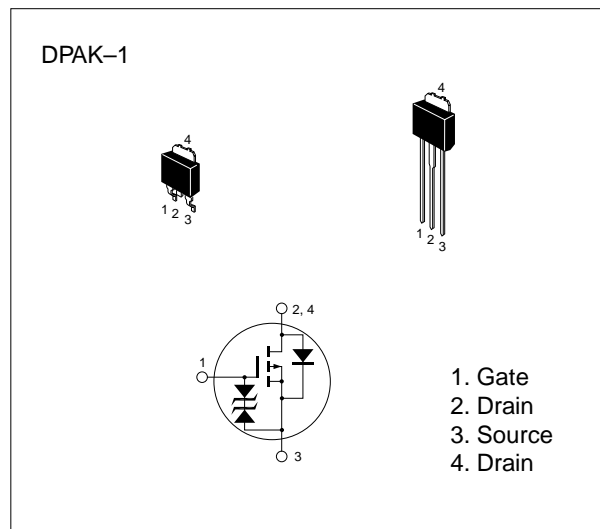


Table 1 Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

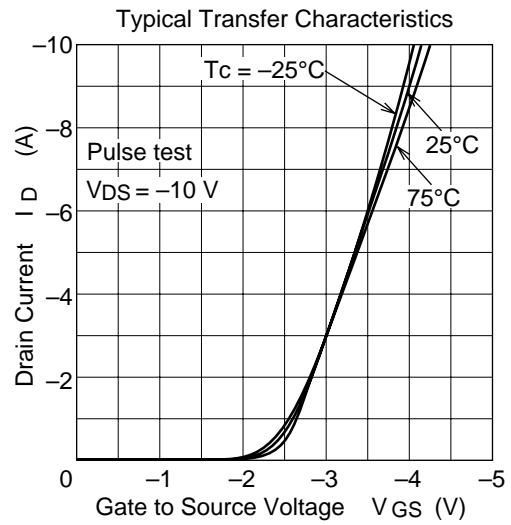
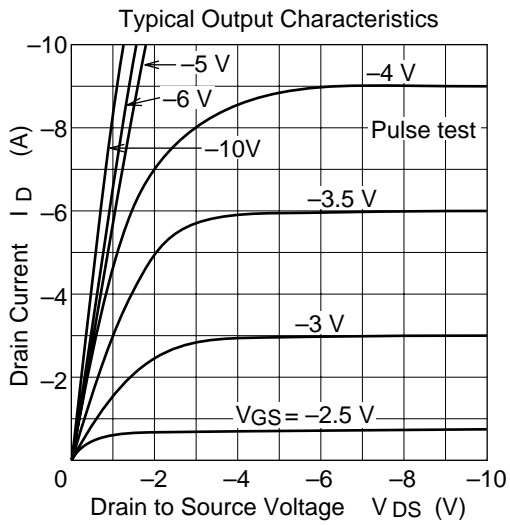
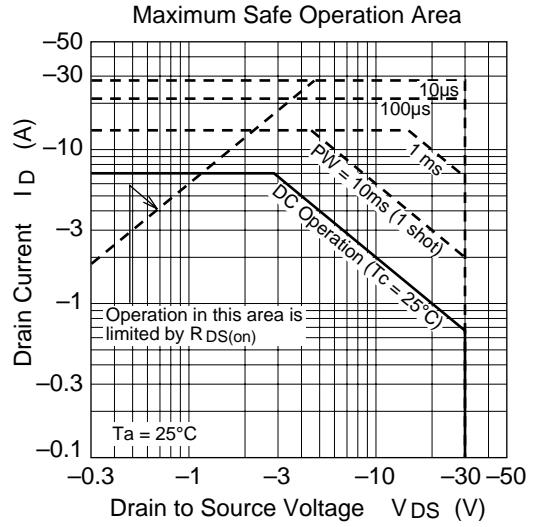
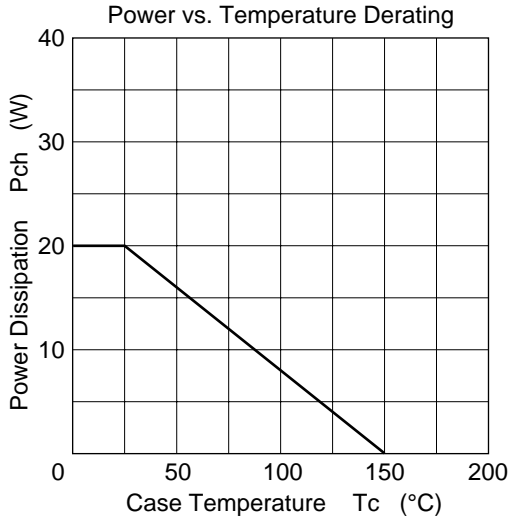
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-30	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	-7	A
Drain peak current	$I_{D(\text{pulse})}^*$	-28	A
Body-drain diode reverse drain current	I_{DR}	-7	A
Channel dissipation	P_{ch}^{**}	20	W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

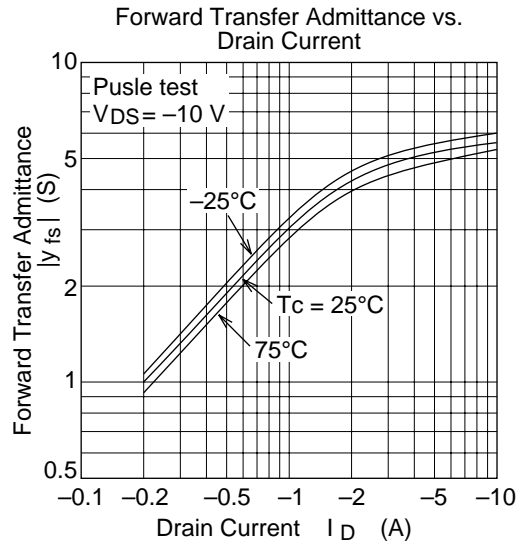
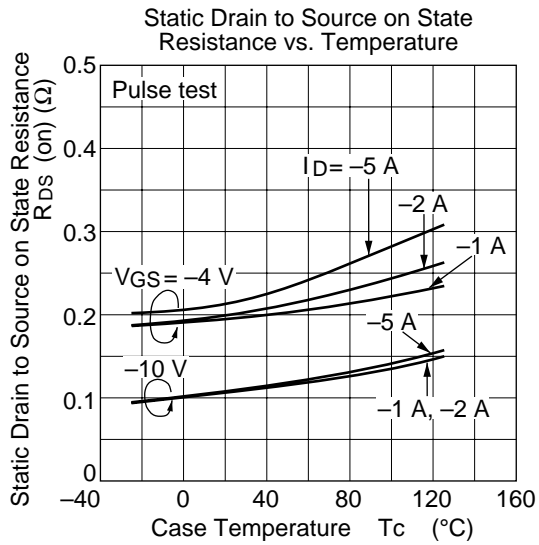
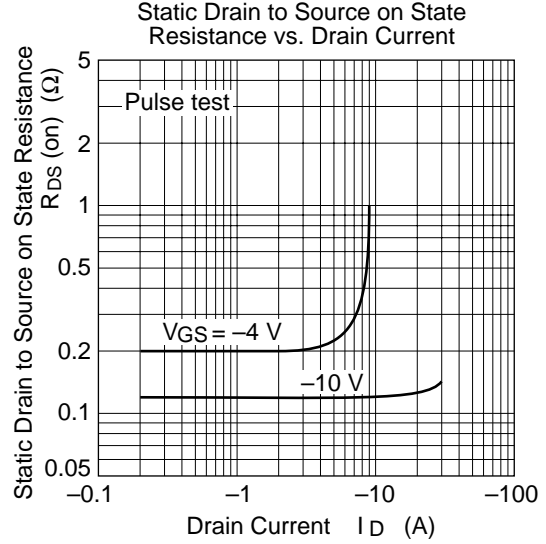
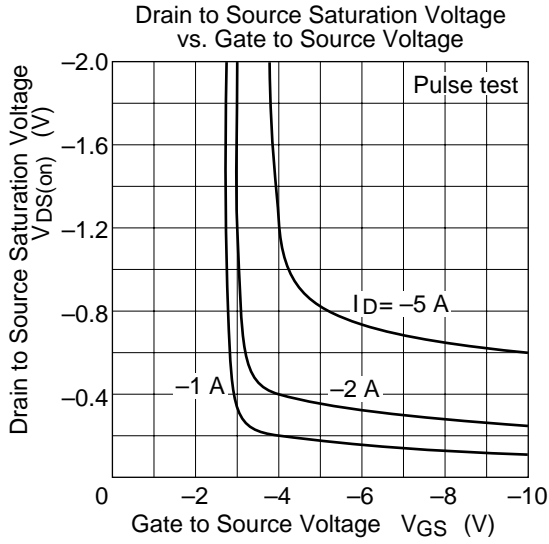
* $PW \leq 10 \mu\text{s}$, duty cycle $\leq 1\%$

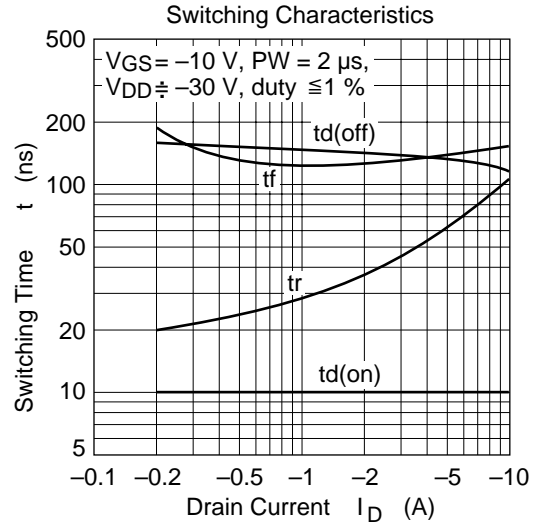
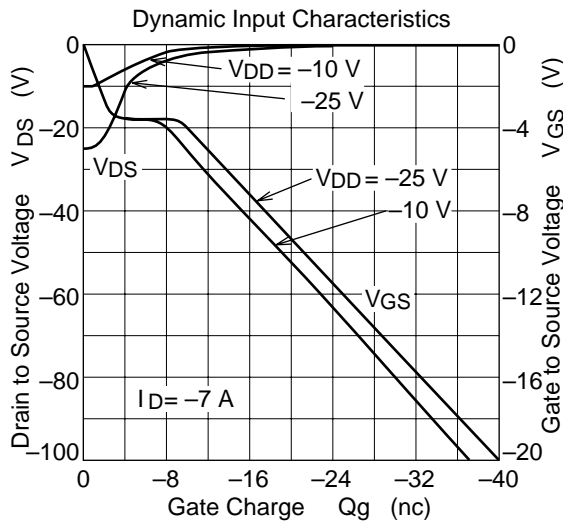
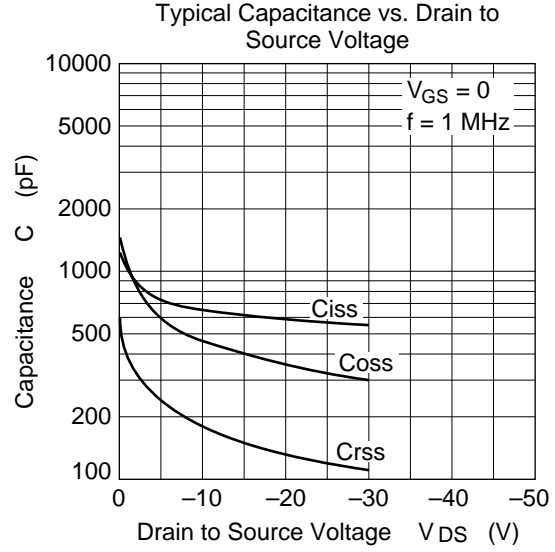
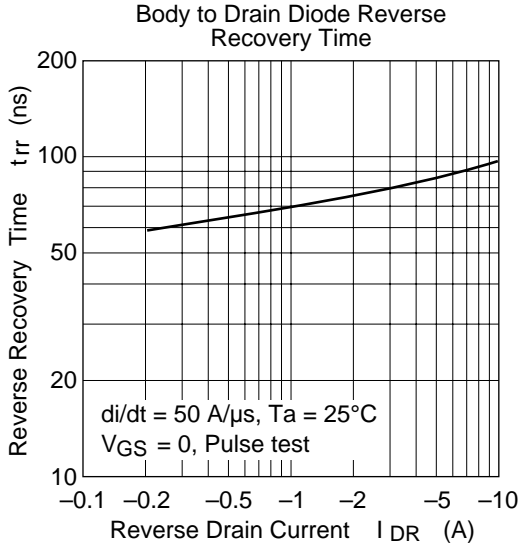
** Value at $T_c = 25^\circ\text{C}$

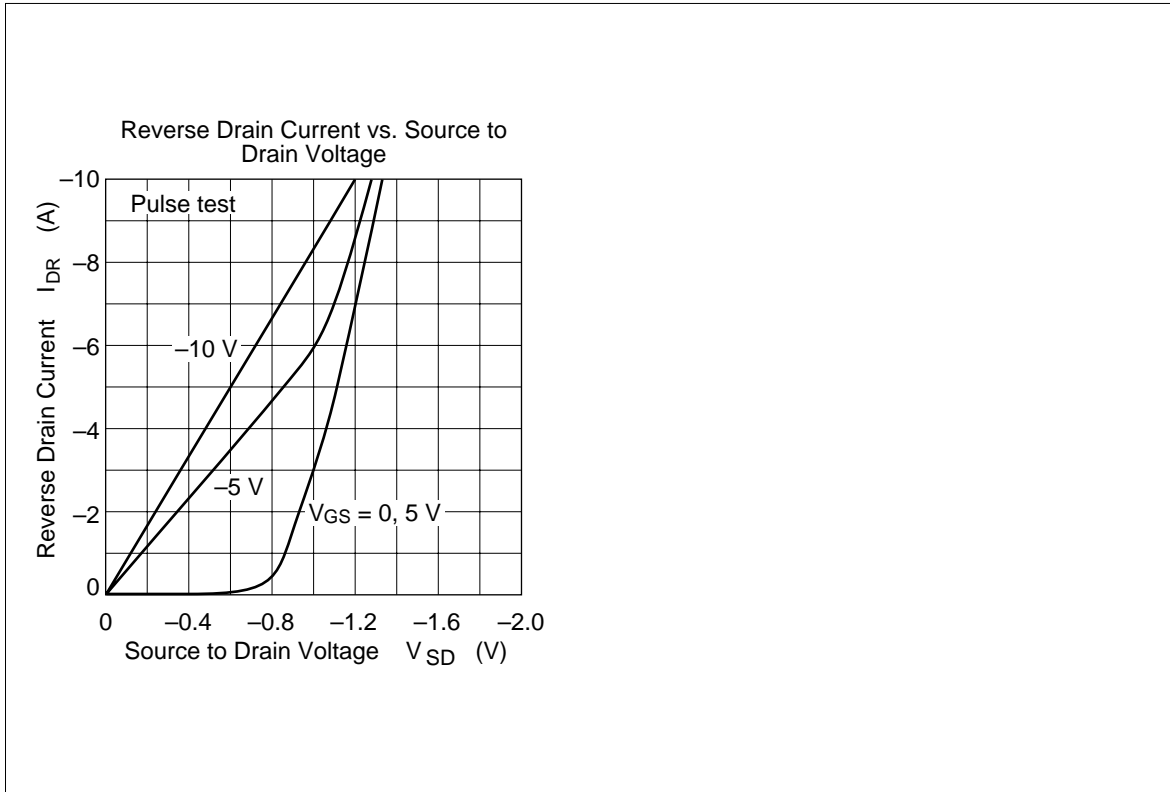
Table 2 Electrical Characteristics (Ta = 25°C)

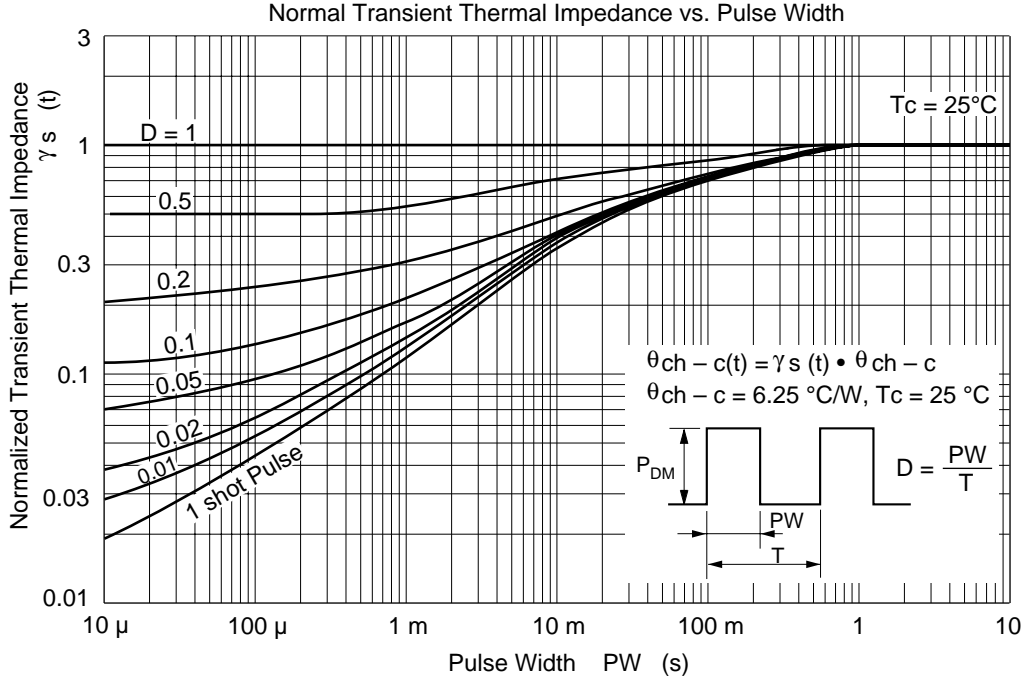
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-30	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-100	μA	$V_{DS} = -25 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.5	V	$V_{DS} = -10 \text{ V}$, $I_D = -1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.12	0.17	Ω	$I_D = -4 \text{ A}$ $V_{GS} = -10 \text{ V}$
		—	0.21	0.31	Ω	$I_D = -4 \text{ A}$ $V_{GS} = -4 \text{ V}$
Forward transfer admittance	$ y_{fs} $	3.0	5.0	—	S	$V_{DS} = -10 \text{ V}$ $I_D = -4 \text{ A}$
Input capacitance	C_{iss}	—	660	—	pF	$V_{DS} = -10 \text{ V}$
Output capacitance	C_{oss}	—	465	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	180	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$V_{GS} = -10 \text{ V}$
Rise time	t_r	—	55	—	ns	$I_D = -4 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	135	—	ns	$R_L = 7.5 \text{ }\Omega$
Fall time	t_f	—	135	—	ns	
Body-drain diode forward voltage	V_{DF}	—	-1.2	—	V	$I_F = -7 \text{ A}$, $V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	90	—	μs	$I_F = -7 \text{ A}$, $V_{GS} = 0$, $di_F / dt = 50 \text{ A} / \mu\text{s}$











Switching Time Test Circuit Waveform

